
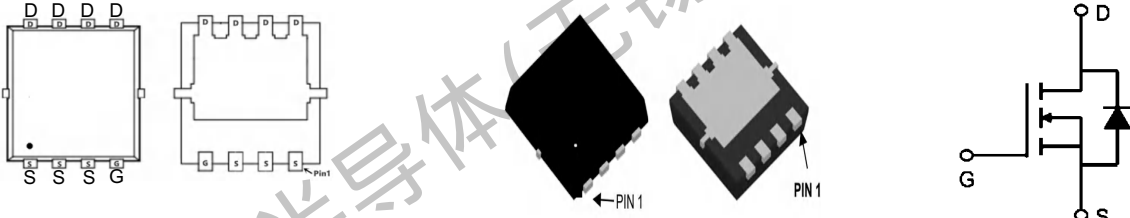


TMG120N04NF

N-Channel Enhancement Mosfet

| | |
|--|--|
| <p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM | <p>General Features</p> <p>$V_{DS} = 40V$ $I_D = 120A$</p> <p>$R_{DS(ON)} = 2.2 m\Omega (typ.) @ V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p>  |
|--|--|

NF:DFN5x6-8L



Marking: G120N04

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|---------------------------|--|------------|------------|
| V_{DS} | Drain-Source Voltage | 40 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 120 | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 70 | A |
| I_{DM} | Pulsed Drain Current | 400 | A |
| EAS | Single Pulse Avalanche Energy | 121 | mJ |
| I_{AS} | Avalanche Current | --- | A |
| $P_D @ T_C = 25^\circ C$ | Total Power Dissipation | 85 | W |
| T_{STG} | Storage Temperature Range | -55 to 175 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 175 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|-------------------------------------|------|------|--------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient | --- | 50 | $^\circ C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case | --- | 1.47 | $^\circ C/W$ |

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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|--|--|------|-----------|------------|
| Off Characteristics | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=250 \mu A$ | 40 | --- | --- | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{GS}=0V, V_{DS}=40V$ | --- | --- | 1 | μA |
| I_{GSS} | Gate-Source Leakage Current | $V_{GS}=\pm 20V, V_{DS}=0A$ | --- | --- | ± 100 | nA |
| On Characteristics | | | | | | |
| $V_{GS(th)}$ | Gate-Source Threshold Voltage | $V_{GS}=V_{DS}, I_D=250 \mu A$ | 1.2 | 1.6 | 2.0 | V |
| $R_{DS(on)}$ | Drain-Source On Resistance ³ | $V_{GS}=10V, I_D=15A$ | --- | 2.2 | 2.8 | $m \Omega$ |
| | | $V_{GS}=4.5V, I_D=10A$ | --- | 3.3 | 4 | $m \Omega$ |
| Dynamic Characteristics | | | | | | |
| C_{iss} | Input Capacitance | $V_{DS}=20V, V_{GS}=0V, f=1MHz$ | --- | 1974 | --- | pF |
| C_{oss} | Output Capacitance | | --- | 1073 | -- | |
| C_{rss} | Reverse Transfer Capacitance | | --- | 46 | --- | |
| Switching Characteristics | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DS}=20V, I_D=50A,$ $R_{ENG}=1.6 \Omega, V_{GS}=10V$ | --- | 14 | --- | ns |
| t_r | Rise Time | | --- | 5 | --- | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | --- | 47 | --- | ns |
| t_f | Fall Time | | --- | 11 | --- | ns |
| Q_g | Total Gate Charge | | $V_{GS}=10V, V_{DS}=20V,$ $I_D=50A$ | --- | 34.6 | --- |
| Q_{gs} | Gate-Source Charge | --- | | 6.2 | --- | nC |
| Q_{gd} | Gate-Drain "Miller" Charge | --- | | 5.6 | --- | nC |
| Drain-Source Diode Characteristics | | | | | | |
| V_{SD} | Diode Forward Voltage | $V_{GS}=0V, I_{SD}=15A$ | --- | --- | 1.2 | V |
| I_S | Continuous Drain Current | $V_D=V_G=0V$ | --- | --- | 120 | A |
| I_{SM} | Pulsed Drain Current | | --- | --- | 400 | A |
| T_{rr} | Reverse Recovery Time | $I_F=50A,$ | --- | 68 | --- | ns |
| Q_{rr} | Reverse Recovery Charge | $dI/dt=100A/\mu s$ | --- | 14 | --- | nC |



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Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

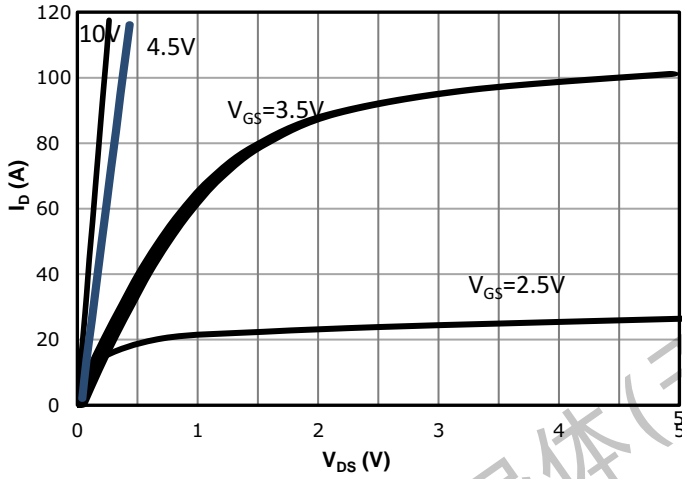


Fig 1: Output Characteristics

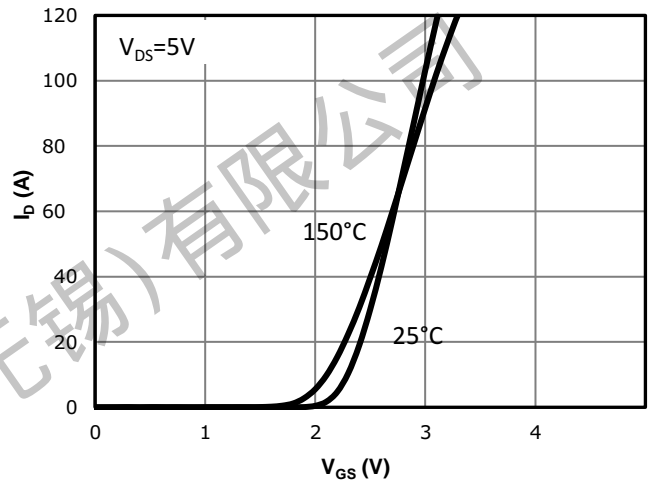


Fig 2: Transfer Characteristics

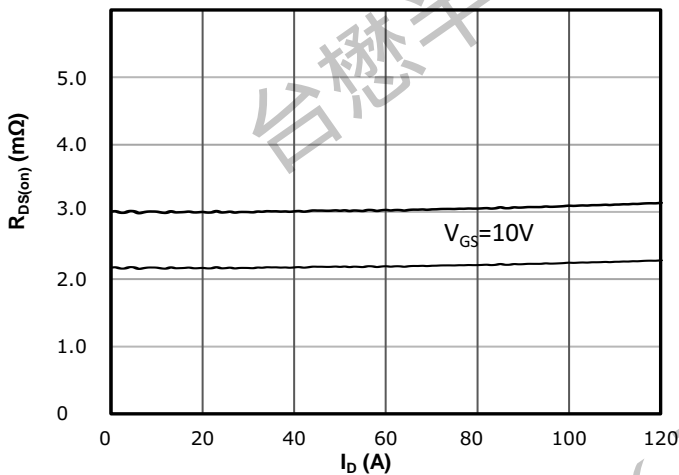


Fig 3: Rds(on) vs Drain Current and Gate Voltage

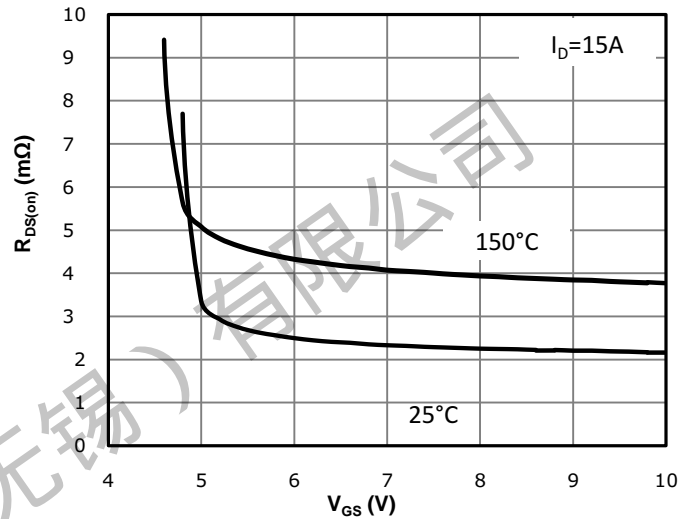


Fig 4: Rds(on) vs Gate Voltage

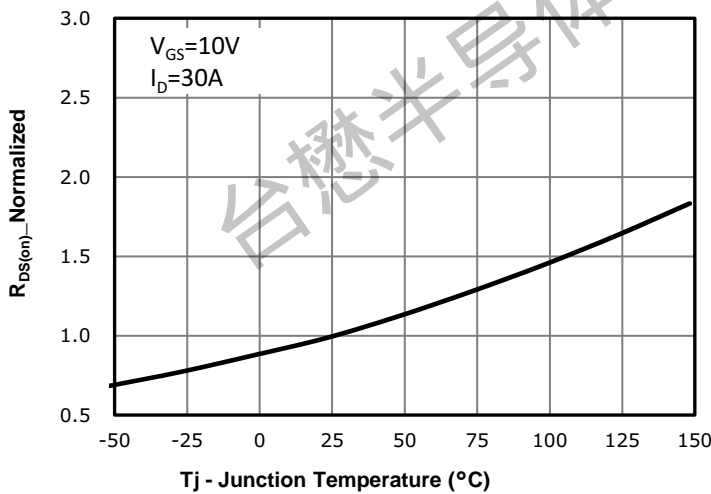


Fig 5: Rds(on) vs. Temperature

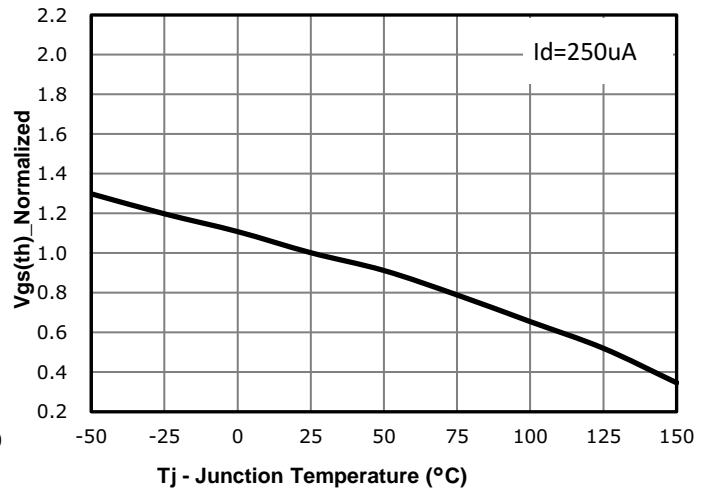


Fig 6: Vgs(th) vs. Temperature



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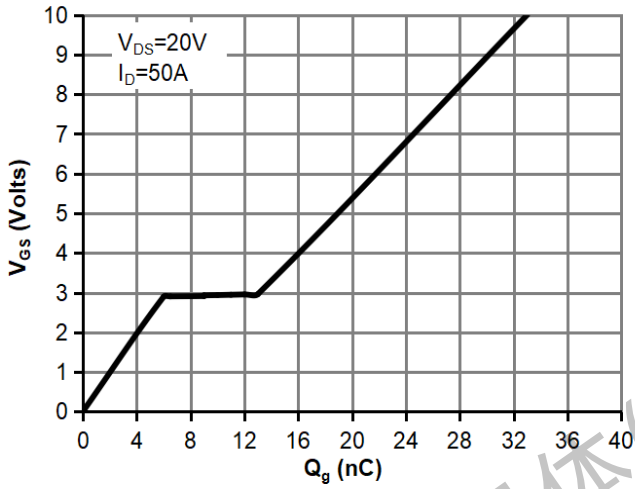


Fig 7: Gate Charge Characteristics

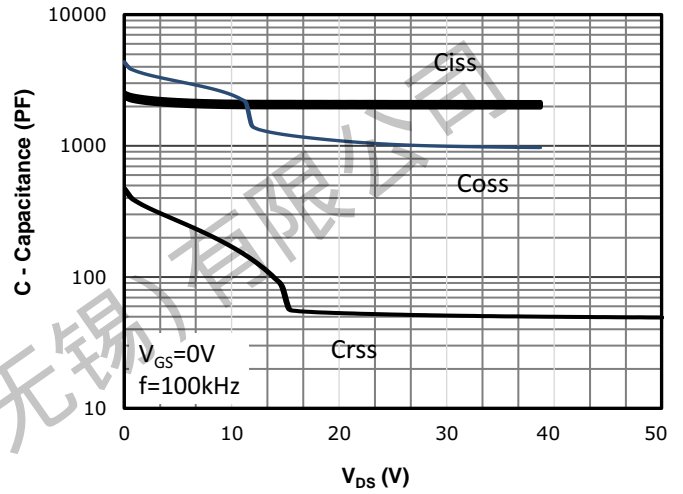


Fig 8: Capacitance Characteristics

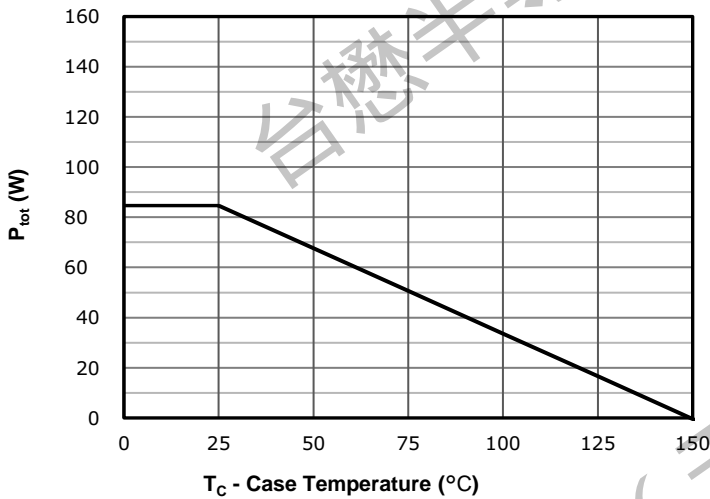


Fig 9: Power Dissipation

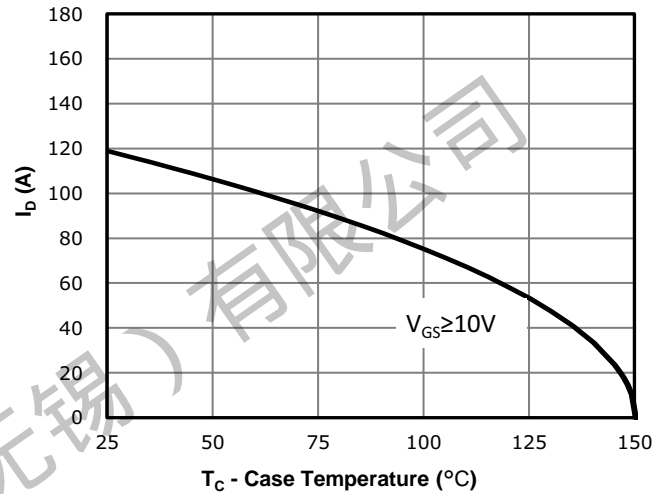


Fig 10: Drain Current Derating

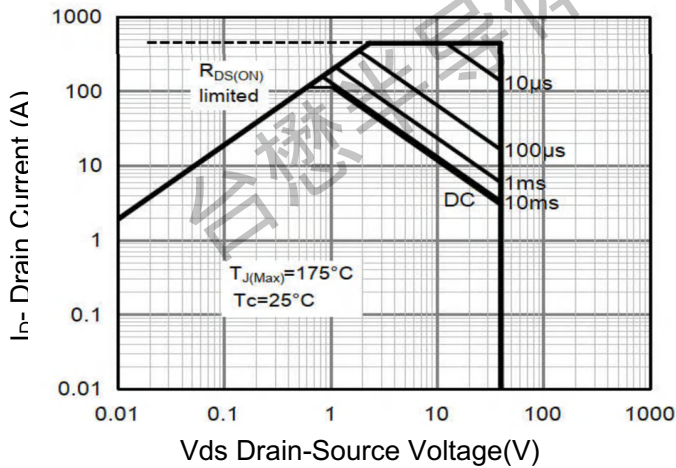


Figure 11 Safe Operation Area

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N-Channel Enhancement Mosfet

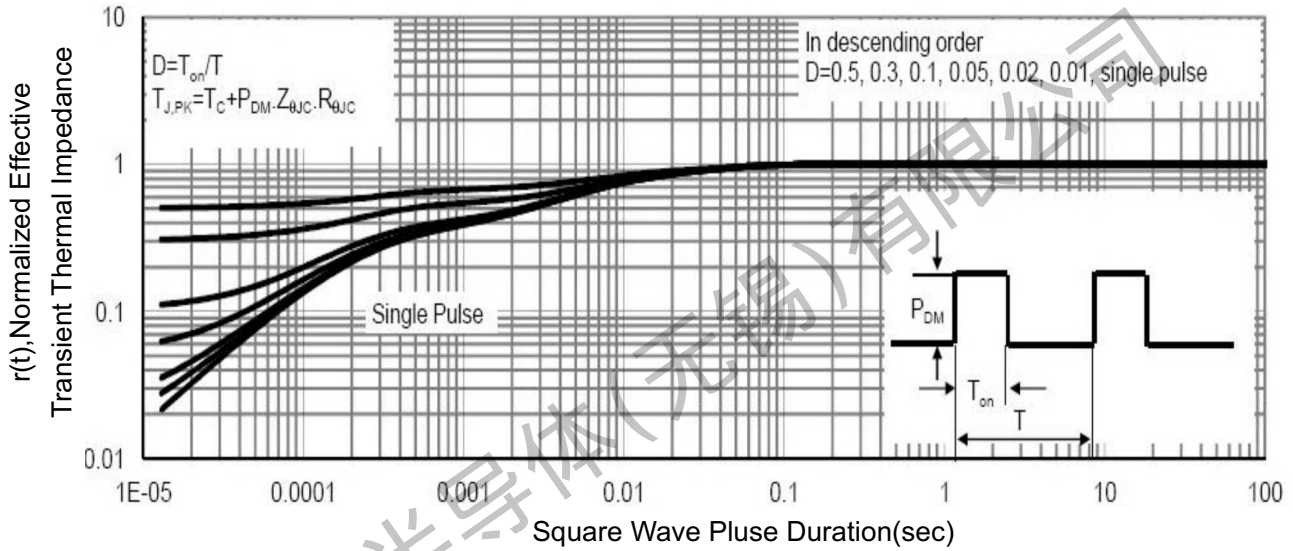
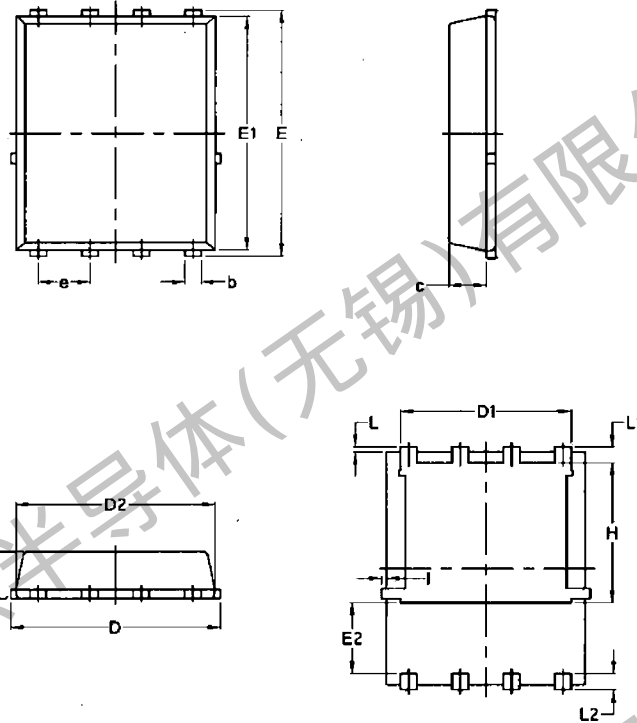


Figure 12 Normalized Maximum Transient Thermal Impedance

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N-Channel Enhancement Mosfet

Package Mechanical Data:DFN5x6-8L

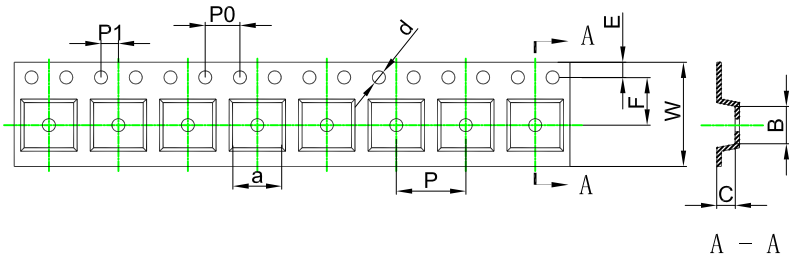


| Symbol | Common | | | |
|--------|----------|--------|----------|--------|
| | mm | | Inch | |
| | Min | Max | Min | Max |
| A | 1.03 | 1.17 | 0.0406 | 0.0461 |
| b | 0.34 | 0.48 | 0.0134 | 0.0189 |
| c | 0.824 | 0.0970 | 0.0324 | 0.082 |
| D | 4.80 | 5.40 | 0.1890 | 0.2126 |
| D1 | 4.11 | 4.31 | 0.1618 | 0.1697 |
| D2 | 4.80 | 5.00 | 0.1890 | 0.1969 |
| E | 5.95 | 6.15 | 0.2343 | 0.2421 |
| E1 | 5.65 | 5.85 | 0.2224 | 0.2303 |
| E2 | 1.60 | / | 0.0630 | / |
| e | 1.27 BSC | | 0.05 BSC | |
| L | 0.05 | 0.25 | 0.0020 | 0.0098 |
| L1 | 0.38 | 0.50 | 0.0150 | 0.0197 |
| L2 | 0.38 | 0.50 | 0.0150 | 0.0197 |
| H | 3.30 | 3.50 | 0.1299 | 0.1378 |
| I | / | 0.18 | / | 0.0070 |

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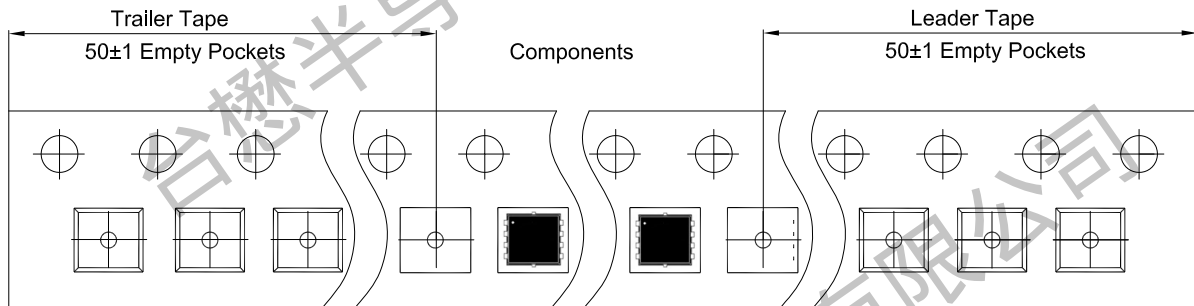
PDFN5x6-8L Embossed Carrier Tape



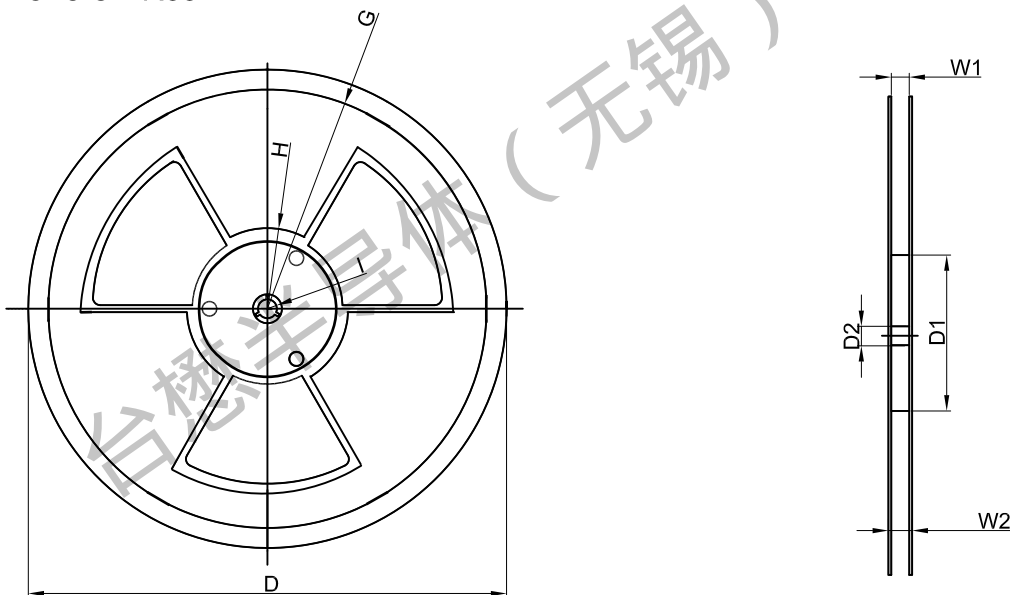
Packaging Description:
SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).
ALL DIM IN mm

| Dimensions are in millimeter | | | | | | | | | | |
|------------------------------|------|------|------|-------|------|------|------|------|------|-------|
| Pkg type | a | B | C | d | E | F | P0 | P | P1 | W |
| PDFN5x6-8L | 6.40 | 5.40 | 2.10 | Ø1.50 | 1.75 | 5.50 | 4.00 | 8.00 | 2.00 | 12.00 |

PDFN5x6-8L Tape Leader and Trailer



PDFN5x6-8L Reel



| Dimensions are in millimeter | | | | | | | | |
|------------------------------|---------|--------|-------|---------|--------|-------|-------|-------|
| Reel Option | D | D1 | D2 | G | H | I | W1 | W2 |
| 13"Dia | Ø330.00 | 100.00 | 13.00 | R135.00 | R55.00 | R6.50 | 12.00 | 14.00 |

| REEL | Reel Size | Box | Box Size(mm) | Carton | Carton Size(mm) | G.W.(kg) |
|-----------|-----------|------------|--------------|------------|-----------------|----------|
| 5,000 pcs | 13 inch | 10,000 pcs | 370×355×52 | 50,000 pcs | 400×360×368 | |



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Revision history:

| Date | Rev | Description | Page |
|------------|-------|-------------|------|
| 2023.07.28 | 23.07 | Original | |